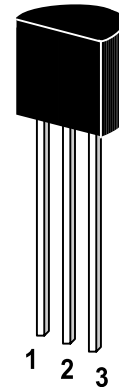


ST 2SA1267

PNP Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y
and G according to its DC current gain.

On special request, these transistors can be
manufactured in different pin configurations.



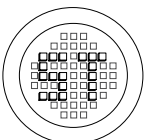
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package
Weight approx. 0.19g

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Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Emitter Current	I_E	150	mA
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +125	$^\circ\text{C}$

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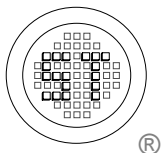
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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

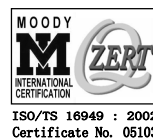
	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE}=6\text{V}$, $-I_C=2\text{mA}$	Current Gain Group O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
	G	h_{FE}	200	-	400	-
Collector Cutoff Current at $-V_{CB}=50\text{V}$	$-I_{CBO}$	-	-	0.1	μA	
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	μA	
Collector Emitter Saturation Voltage at $-I_C=100\text{mA}$, $-I_B=10\text{mA}$	$-V_{CE(sat)}$	-	0.1	0.3	V	
Transition Frequency at $-V_{CE}=10\text{V}$, $-I_E=1\text{mA}$	f_T	80	-	-	MHz	
Noise Figure at $-V_{CE}=6\text{V}$, $-I_C=0.1\text{V}$, $f=1\text{KHZ}$, $R_G=10\text{k}\Omega$	NF	-	1	10	dB	
Collector Output Capacitance at $-V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{OB}	-	4	7	pF	

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SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 7/12/2002